IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:	Eliyahou Harari et al.		
Title:	Multi-State Non-Volatile Integrated Circuit Memory Systems That Employ Dielectric Storage Elements		
Application No.:	10/002,696	Filing Date:	October 31, 2001
Examiner:	Weiss, Howard	Group Art Unit:	2814
Docket No.:	SNDK.272US0	Conf. No.:	4652

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, Applicants call the documents listed on the enclosed Form PTO-1449 to the Examiner's attention in this patent application. Copies of the documents listed on the accompanying Form PTO-1449 are enclosed.

Citation of these documents shall not be construed as (1) an admission that the documents are prior art with respect to the invention or inventions claimed in this application, (2) a representation that a search has been made (other than as indicated by any cited document), or (3) an admission that the cited information is, or is considered to be, material to patentability as defined in § 1.56(b).

This information disclosure statement is submitted under 37 C.F.R. § 1.97(b) and consequently no fee should be required. The Commissioner is authorized, however, to charge any fee that may be required, or to credit any overpayment, against Deposit Account No. 502664.

EXPRESS MAIL LABEL NO:

EV437668995US

Respectfully submitted,

October 26, 2004

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U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
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U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	1	6,670,240 B2	12/30/03	Ogura et al.			
	2	6,413,821 B1	7/2/02	Ebina et al.			
	3	6,388,293 B1	5/14/02	Ogura et al.			
	4	6,399,441 B1	6/4/02	Ogura et al.			
	5	6,177,318 B1	1/23/01	Ogura et al.			
	6	6,418,062 B1	7/9/02	Hayashi et al.			
	7	6,459,622 B1	10/1/02	Ogura et al.			
	8	6,477,088 B2	11/5/02	Ogura et al.			
	9	6,636,438 B2	10/21/03	Ogura et al.			

U.S. Published Patent Application Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	10	11224940	8/17/99	Japan			Abstract	X

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	11	S. Ogura et al., "Low Voltage, Low Current, High Speed Program Step Split Gate Cell With Ballistic Direct Injection for EEPROM/Flash", 1998, IEDM Technical Digest, 36.5, pp. 987-990.
	12	F.I. Hampton et al., "Space Charge Distribution Limitation on Scale Down of MNOS Memory Devices", 1979, IEDM Technical Digest, pp. 374-377.
	13	Eiichi Suzuki et al., "A Low-Voltage Alterable EEPROM With Metal-Oxide-Nitride-Oxide-Semiconductor (MONOS) Structures", IEEE Transactions on Electron Devices, Vol. ED-30, No. 2, February, 1883, pp. 122-128.

Examiner	Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	14	6,709,922 B2	3/23/04	Ebina et al.			
	15	6,735,118 B2	5/11/04	Ogura et al.			
	16	6,531,350 B2	3/11/03	Satoh et al.			
	17	6,255,166 B1	7/3/01	Ogura et al.			
	18	6,549,463 B2	4/15/03	Ogura et al.			
	19	6,531,732 B2	3/11/03	Sugita et al.			
	20	5,946,231	8/31/99	Endoh et al.			

U.S. Published Patent Application Documents

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Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	21	Y. Tarui et al., "Electrically Reprogrammable Nonvolatile Semiconductor Memory", IEEE Journal of Solid State Circuits, Vol, SC-7, No. 5, October 1972, pp. 369-375.
	22	Boaz Eitan et al., "Can NROM, a 2 Bit, Trapping Storage NMV Cell, Give a Real Challenge to Floating Gate Cells?", Extended Abstracts, 1999 Conference on Solid State Devices and Materials, Tokyo, 1999, pp. 522-524.

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